Fei Hui

List of Publications by Year
in descending order

26	2,256	516710 16	642732 23
papers	citations	h-index	g-index

27	27	27	2652
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Electronic synapses made of layered two-dimensional materials. Nature Electronics, 2018, 1, 458-465.	26.0	459
2	Recommended Methods to Study Resistive Switching Devices. Advanced Electronic Materials, 2019, 5, 1800143.	5.1	452
3	Coexistence of Grainâ€Boundariesâ€Assisted Bipolar and Threshold Resistive Switching in Multilayer Hexagonal Boron Nitride. Advanced Functional Materials, 2017, 27, 1604811.	14.9	229
4	Wafer-scale integration of two-dimensional materials in high-density memristive crossbar arrays for artificial neural networks. Nature Electronics, 2020, 3, 638-645.	26.0	222
5	Graphene and Related Materials for Resistive Random Access Memories. Advanced Electronic Materials, 2017, 3, 1600195.	5.1	175
6	A Review on Dielectric Breakdown in Thin Dielectrics: Silicon Dioxide, Highâ€k, and Layered Dielectrics. Advanced Functional Materials, 2020, 30, 1900657.	14.9	119
7	A Review on Principles and Applications of Scanning Thermal Microscopy (SThM). Advanced Functional Materials, 2020, 30, 1900892.	14.9	98
8	On the use of two dimensional hexagonal boron nitride as dielectric. Microelectronic Engineering, 2016, 163, 119-133.	2.4	96
9	Resistive Random Access Memory Cells with a Bilayer TiO₂/SiO_X Insulating Stack for Simultaneous Filamentary and Distributed Resistive Switching. Advanced Functional Materials, 2017, 27, 1700384.	14.9	70
10	Advanced Data Encryption â€‹using 2D Materials. Advanced Materials, 2021, 33, e2100185.	21.0	67
11	Model for multi-filamentary conduction in graphene/hexagonal-boron-nitride/graphene based resistive switching devices. 2D Materials, 2017, 4, 025099.	4.4	51
12	Inkjet Printed Circuits with 2D Semiconductor Inks for Highâ€Performance Electronics. Advanced Electronic Materials, 2021, 7, 2100112.	5.1	46
13	Synthesis of large-area multilayer hexagonal boron nitride sheets on iron substrates and its use in resistive switching devices. 2D Materials, 2018, 5, 031011.	4.4	45
14	Repeated roll-to-roll transfer of two-dimensional materials by electrochemical delamination. Nanoscale, 2018, 10, 5522-5531.	5.6	28
15	150Ânm Ã— 200Ânm Crossâ€Point Hexagonal Boron Nitrideâ€Based Memristors. Advanced Electronic Materials, 2020, 6, 1900115.	5.1	22
16	In Situ Observation of Lowâ€Power Nanoâ€Synaptic Response in Graphene Oxide Using Conductive Atomic Force Microscopy. Small, 2021, 17, e2101100.	10.0	22
17	Variability of metal/h-BN/metal memristors grown via chemical vapor deposition on different materials. Microelectronics Reliability, 2019, 102, 113410.	1.7	17
18	(Invited) Elucidating the Origin of Resistive Switching in Ultrathin Hafnium Oxides through High Spatial Resolution Tools. ECS Transactions, 2014, 64, 19-28.	0.5	13

#	Article	IF	Citations
19	Emerging Scanning Probeâ€“Based Setups for Advanced Nanoelectronic Research. Advanced Functional Materials, 2020, 30, 1902776.	14.9	7
20	Constructing van der Waals heterostructures by dry-transfer assembly for novel optoelectronic device. Nanotechnology, 2022, 33, 465601.	2.6	7
21	Resistive Switching: Coexistence of Grainâ€Boundariesâ€Assisted Bipolar and Threshold Resistive Switching in Multilayer Hexagonal Boron Nitride (Adv. Funct. Mater. 10/2017). Advanced Functional Materials, 2017, 27, .	14.9	4
22	150 nm Ã— 200 nm cross point hexagonal boron nitride based memristors with ultra-low currents in high resistive state. , 2019, , .		3
23	Time series modeling of the cycle-to-cycle variability in h-BN based memristors. , 2021, , .		2
24	Inkjet Printing: A Cheap and Easyâ€toâ€Use Alternative to Wire Bonding for Academics. Crystal Research and Technology, 2022, 57, 2100210.	1.3	1
25	Reversible dielectric breakdown in h-BN stacks: a statistical study of the switching voltages. , 2020, , .		0
26	Influence of the magnetic field on dielectric breakdown in memristors based on h-BN stacks. , 2020, , .		0